

ABSTRACT OF THE DISCLOSURE

Peripheries of a contact 26 for connecting a polycrystalline silicon layer 20 to a pixel electrode 28 are 5 cut by a laser to form a cut area 50. By this cut area 50, the polycrystalline silicon layer 20 around the contact 26 is also cut. In consequence, a TFT 24 is separated from the pixel electrode 28 and a supplemental capacitor electrode 32 to reliably accomplish darkening.

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